



NPN POWER TRANSISTORS

COMPLEMENTARY TO THE TIP30 SERIES

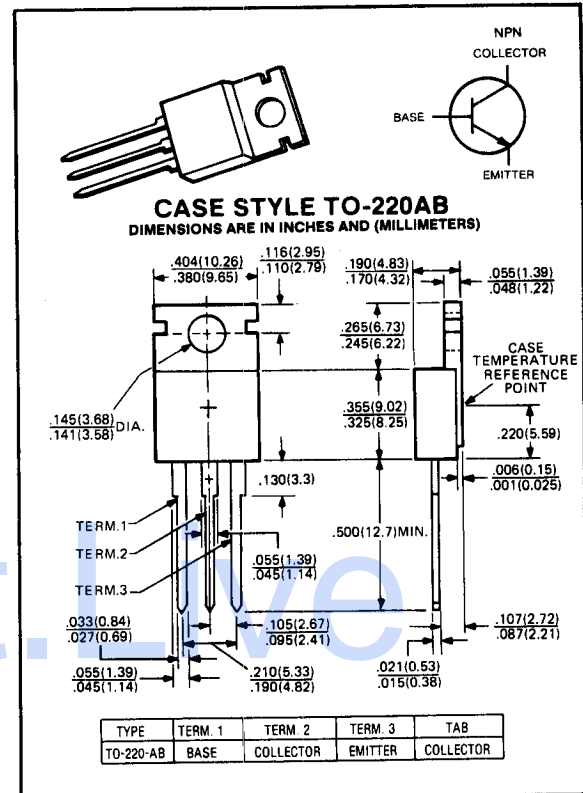
TIP 29 Series

40-100 VOLTS
1 AMP, 30 WATTS

The TIP29 Series power transistors are designed for use in general purpose amplifier and switching applications.

Features:

- Designed for complementary use with TIP30 series
- 30W at 25°C case temperature
- 1A continuous collector current
- 3A peak collector current
- Minimum f_T of 3 MHz at 10V, 0.02A
- Customer-specified selections available



Datasheet.Live

maximum ratings ($T_C = 25^\circ C$) (unless otherwise noted)

RATING	SYMBOL	TIP29	TIP29A	TIP29B	TIP29C	UNITS
Collector-Emitter Voltage	V_{CEO}	40	60	80	100	Volts
Collector-Base Voltage	V_{CBO}	80	100	120	140	Volts
Emitter Base Voltage	V_{EBO}	5	5	5	5	Volts
Collector Current — Continuous	I_C	1	1	1	1	A
Collector Current — Peak	I_{CM}	3	3	3	3	A
Base Current — Continuous	I_B	0.4	0.4	0.4	0.4	A
Total Power Dissipation @ $T_A = 25^\circ C$ @ $T_C = 25^\circ C$	P_D	2	2	2	2	Watts
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +150	-65 to +150	-65 to +150	-65 to +150	$^\circ C$

thermal characteristics

Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.17	4.17	4.17	4.17	$^\circ C/W$
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	250	250	250	250	$^\circ C$

electrical characteristics ($T_C = 25^\circ C$) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage ($I_C = 30\text{mA}$)	TIP29 TIP29A TIP29B TIP29C	V_{CEO}	40 60 80 100	— — — —	— — — —	Volts
Collector Cutoff Current ($V_{CE} = 30\text{V}$) ($V_{CE} = 60\text{V}$)	TIP29, TIP29A TIP29B, TIP29C	I_{CEO}	— —	— —	0.3 0.3	mA
Collector Cutoff Current ($V_{CE} = 80\text{V}$) ($V_{CE} = 100\text{V}$) ($V_{CE} = 120\text{V}$) ($V_{CE} = 140\text{V}$)	TIP29 TIP29A TIP29B TIP29C	I_{CES}	— — — —	— — — —	0.2 0.2 0.2 0.2	mA
Emitter Cutoff Current ($V_{EB} = 5\text{V}$, $I_C = 0$)		I_{EBO}	—	—	1	mA

second breakdown

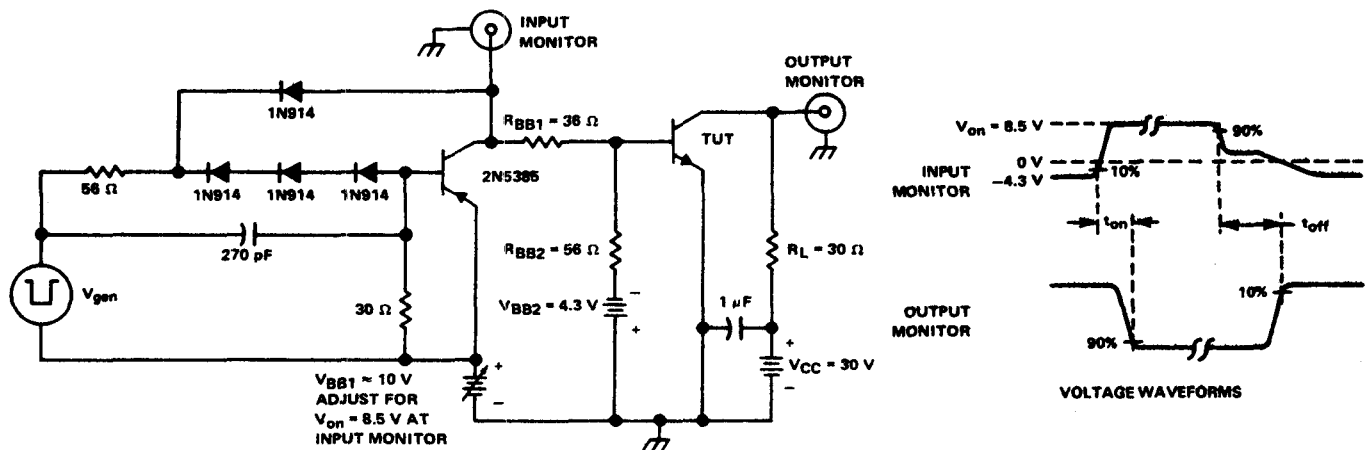
Second Breakdown with Base Forward Biased	FBSOA	SEE FIGURE 3
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on characteristics

DC Current Gain ($I_C = .2\text{A}$, $V_{CE} = 4\text{V}$) ($I_C = 1\text{A}$, $V_{CE} = 4\text{V}$)	h_{FE}	40 15	— —	— 75	—
Collector-Emitter Saturation Voltage ($I_C = 1\text{A}$, $I_B = 125\text{mA}$)	$V_{CE(sat)}$	—	—	0.7	V
Base-Emitter Voltage ($I_C = 1\text{A}$, $V_{CE} = 4\text{V}$)	$V_{BE(on)}$	—	—	1.3	V

switching characteristics

Turn-on Time	$R_L = 30\Omega$, $I_C = 1\text{A}$ $I_{B1} = I_{B2} = 0.1\text{A}$ $V_{BE(off)} = -4.3\text{V}$	t_{on}	—	0.5	—	μs
Turn-off Time		t_{off}	—	2	—	

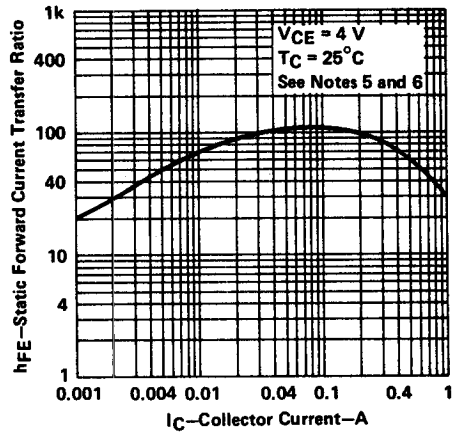


TEST CIRCUIT

- NOTES: A. V_{gen} is a -30-V pulse into a 50Ω termination.
 B. The V_{gen} waveform is supplied by a generator with the following characteristics: $t_r < 15\text{ns}$, $t_f < 15\text{ns}$, $Z_{out} = 50\Omega$, $t_w = 20\mu\text{s}$, duty cycle $\leq 2\%$.
 C. Waveforms are monitored on an oscilloscope with the following characteristics: $t_r < 15\text{ns}$, $R_{in} > 10\text{M}\Omega$, $C_{in} < 11.5\text{pF}$.
 D. Resistors must be noninductive types.
 E. The d-c power supplies may require additional bypassing in order to minimize ringing.

FIGURE 1. RESISTIVE-LOAD SWITCHING

STATIC FORWARD CURRENT TRANSFER RATIO
vs
COLLECTOR CURRENT



NOTES: 5. These parameters must be measured using pulse techniques, $t_w = 300 \mu s$, duty cycle $\leq 2\%$.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

FIGURE 2. TYPICAL CHARACTERISTICS

FORWARD-BIAS SAFE OPERATING AREA

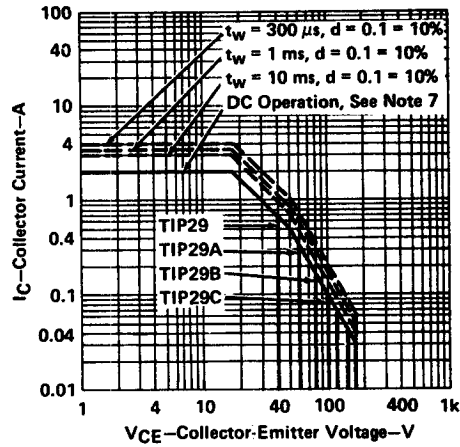


FIGURE 3. MAXIMUM SAFE OPERATING AREA

NOTE 7. This combination of maximum voltage and current may be achieved only when switching from saturation to cutoff with a clamped inductive load.

DISSIPATION DERATING CURVE

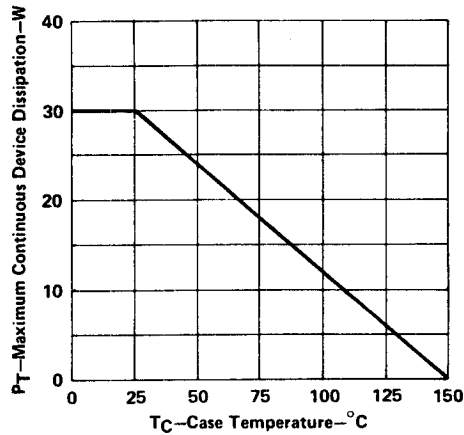


FIGURE 4. THERMAL INFORMATION